MPSA14 is a Preferred Device

Darlington Transistors NPN Silicon

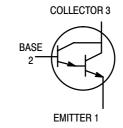
Features

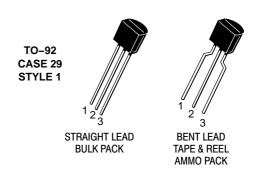
• Pb-Free Packages are Available*



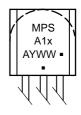
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



x = 3 or 4 A = Assembly Location Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CES}	30	Vdc
Collector-Base Voltage	V _{CBO}	30	Vdc
Emitter-Base Voltage	V _{EBO}	10	Vdc
Collector Current – Continuous	Ι _C	500	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/mW
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/mW

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS			•		•
Collector – Emitter Breakdown Voltage $(I_C = 100 \ \mu Adc, I_B = 0)$		V _{(BR)CES}	30	-	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I _E = 0)		I _{CBO}	-	100	nAdc
Emitter Cutoff Current (V_{EB} = 10 Vdc, I_C = 0)		I _{EBO}	-	100	nAdc
ON CHARACTERISTICS (Note 1)			•		•
DC Current Gain (I _C = 10 mAdc, V _{CE} = 5.0 Vdc) (I _C = 100 mAdc, V _{CE} = 5.0 Vdc)	MPSA13 MPSA14 MPSA13 MPSA14	h _{FE}	5,000 10,000 10,000 20,000		-
Collector – Emitter Saturation Voltage ($I_C = 100 \text{ mAdc}, I_B = 0.1 \text{ mAdc}$)		V _{CE(sat)}	-	1.5	Vdc
Base – Emitter On Voltage ($I_C = 100 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)		V _{BE(on)}	-	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product (Note 2) (I _C = 10 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	125	-	MHz

1. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle \leq 2.0%.

2. $f_T = |h_{fe}| \bullet f_{test}$.

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSA13	TO-92	5000 Units / Bulk
MPSA13G	TO–92 (Pb–Free)	5000 Units / Bulk
MPSA13RLRA	TO-92	2000 / Tape & Reel
MPSA13RLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel
MPSA13RLRMG	TO–92 (Pb–Free)	2000 / Ammo Pack
MPSA13RLRPG	TO–92 (Pb–Free)	2000 / Ammo Pack
MPSA13ZL1G	TO–92 (Pb–Free)	2000 / Ammo Pack
MPSA14G	TO–92 (Pb–Free)	5000 Units / Bulk
MPSA14RLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel
MPSA14RLRPG	TO–92 (Pb–Free)	2000 / Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

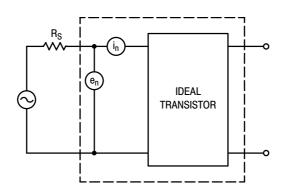
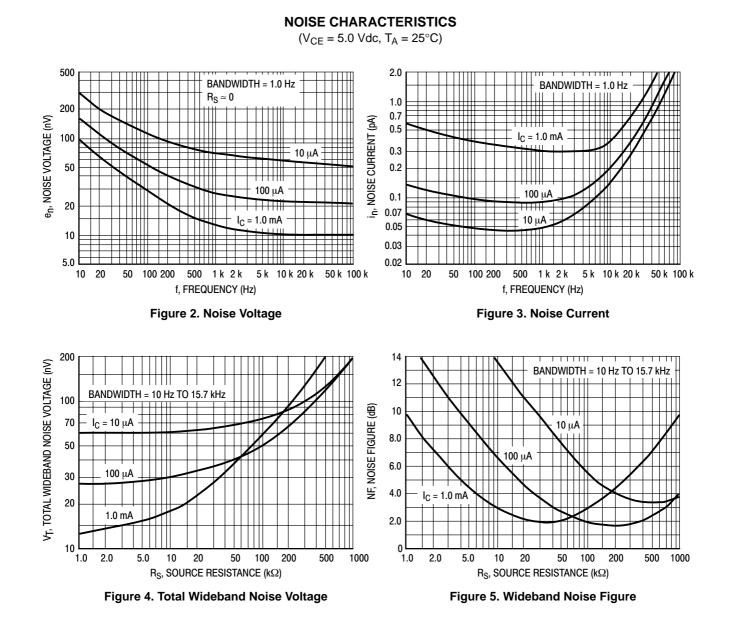


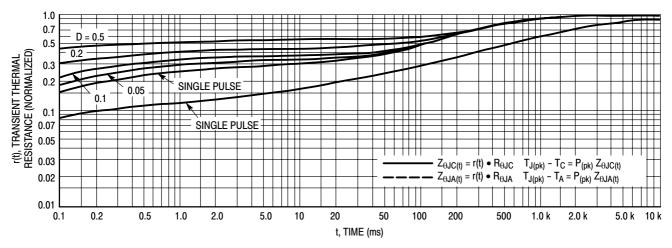
Figure 1. Transistor Noise Model

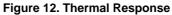


20 4.0 V_{CE} = 5.0 V SMALL-SIGNAL CURRENT GAIN f = 100 MHz $T_J = 25^{\circ}C$ $T_J=25^\circ C$ 2.0 10 Ш C, CAPACITANCE (pF) 7.0 Cibo 1.0 Cobo 0.8 5.0 0.6 3.0 0.4 hfel, 2.0 0.2 2.0 20 2.0 0.5 100 200 0.1 0.2 0.4 4.0 10 1.0 10 20 50 500 0.04 1.0 40 0.5 V_B, REVERSE VOLTAGE (VOLTS) Ic, COLLECTOR CURRENT (mA) Figure 6. Capacitance Figure 7. High Frequency Current Gain 200 k COLLECTOR-EMITTER VOLTAGE (VOLTS) 3.0 T_{.1} = 125°C 25°C 100 k 2.5 70 k 50 mA 250 mA 500 mA hFE, DC CURRENT GAIN I_C = 10 mA 25°C 50 k 2.0 30 k 20 k 1.5 10 k 7.0 k -55 °C 1.0 5.0 k V_{CE} = 5.0 V 3.0 k Ś K 2.0 k 0.5 0.5 30 200 300 500 0.2 2.0 5.0 20 50 100 200 500 1000 5.0 7.0 10 20 50 70 100 0.1 1.0 10 I_C, COLLECTOR CURRENT (mA) I_B, BASE CURRENT (μA) Figure 8. DC Current Gain **Figure 9. Collector Saturation Region** 1.6 -1.0 TEMPERATURE COEFFICIENTS (mV/°C) *APPLIES FOR I_C/I_B \leq h_{FE}/3.0 25°C TO 125°C T_J = 25°C 1 | || *R_{0VC} FOR V_{CE(sat)} 1.4 -2.0 V, VOLTAGE (VOLTS) V_{BE(sat)} @ I_C/I_B = 1000 -55 °C TO 25°C -3.0 1.2 V_{BE(on)} @ V_{CE} = 5.0 V 25°C TO 125°C 1.0 -4.0 ŤΤΙ θ_{VB} FOR V_{BE} 0.8 -5.0 -55 °C TO 25°C V_{CE(sat)} @ I_C/I_B = 1000 R_θý, 0.6 -6.05.0 7.0 50 70 100 200 300 5.0 7.0 10 10 20 30 500 20 30 50 70 100 200 300 500 I_C, COLLECTOR CURRENT (mA) I_C, COLLECTOR CURRENT (mA)

SMALL-SIGNAL CHARACTERISTICS

Figure 10. "On" Voltages





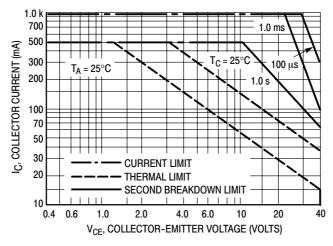
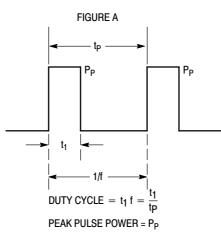


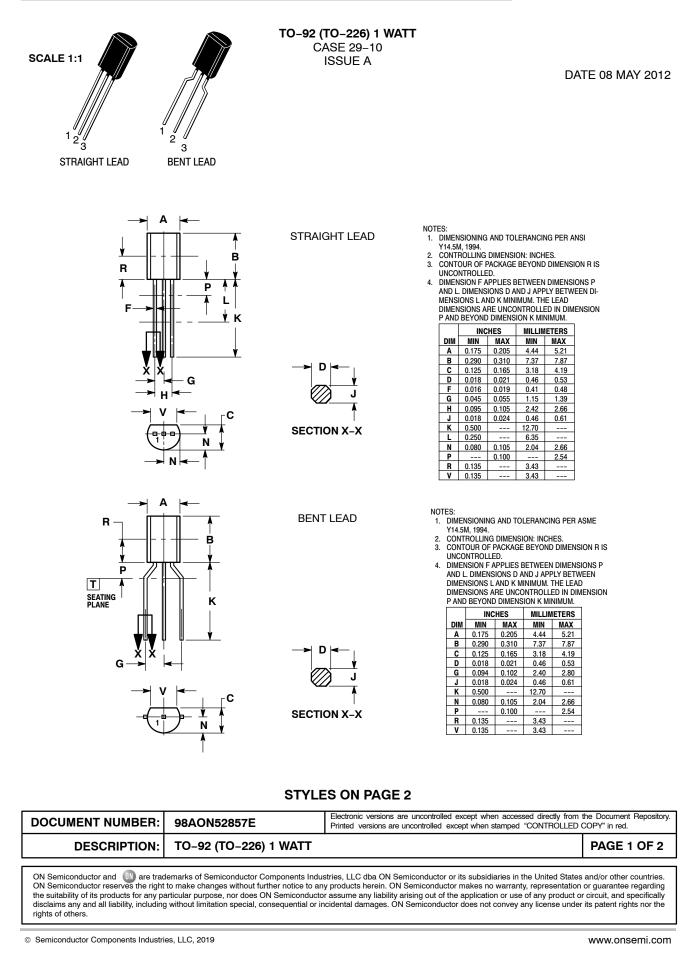
Figure 13. Active Region Safe Operating Area



Design Note: Use of Transient Thermal Resistance Data

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE A

DATE 08 MAY 2012

	EMITTER BASE COLLECTOR								
	GATE SOURCE & SUBSTRATE DRAIN								
STYLE 11: PIN 1. 2. 3.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 Gate Main Terminal 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1 CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
STYLE 21: PIN 1. 2. 3.	COLLECTOR EMITTER BASE	STYLE 22: PIN 1. 2. 3.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2. 3.	EMITTER Collector/Anode Cathode	STYLE 25: PIN 1. 2. 3.	MT 1 GATE MT 2
STYLE 26: PIN 1. 2. 3.	V _{CC} GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	STYLE 28: PIN 1. 2. 3.	CATHODE ANODE GATE	STYLE 29: PIN 1. 2. 3.	NOT CONNECTED ANODE CATHODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE SOURCE
STYLE 31: PIN 1. 2. 3.	GATE DRAIN SOURCE	STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN INPUT OUTPUT	STYLE 34: PIN 1. 2. 3.	INPUT Ground Logic	STYLE 35: PIN 1. 2. 3.	GATE COLLECTOR EMITTER

DOCUMENT NUMBER:	98AON52857E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 2 OF 2		
ON Somiconductor and Marco tradomarko of Somiconductor Componente Inductrice, LLC dae ON Somiconductor or ite subsidiarice in the United States and/or other countries					

ON Semiconductor and us are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor date sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use a a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor houteds for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

ON Semiconductor Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800–282–9855 Toll Free USA/Canada Phone: 011 421 33 790 2910 Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative